

MBR1080G, MBR1090G, MBR10100G, NRVB10100G

SWITCHMODE Power Rectifiers

Features

- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- AEC-Q101 Qualified and PPAP Capable
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb-Free*

Mechanical Characteristics

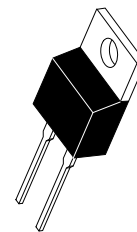
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating:
 - ◆ Human Body Model = 3B
 - ◆ Machine Model = C



ON Semiconductor®

<http://onsemi.com>

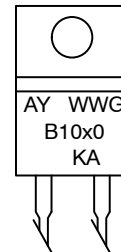
SCHOTTKY BARRIER RECTIFIERS 10 AMPERES, 80 to 100 VOLTS



**TO-220AC
CASE 221B**



MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- B10x0 = Device Code
- x = 8, 9 or 10
- KA = Diode Polarity

ORDERING INFORMATION

| Device | Package | Shipping |
|------------|---------------------|---------------|
| MBR1080G | TO-220 (Pb-Free) | 50 Units/Rail |
| MBR1090G | TO-220 (Pb-Free) | 50 Units/Rail |
| MBR10100G | TO-220 (Pb-Free) | 50 Units/Rail |
| NRVB10100G | TO-220 (Pb-Free) | 50 Units/Rail |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR1080G, MBR1090G, MBR10100G, NRVB10100G

MAXIMUM RATINGS

| Rating | Symbol | MBR/NRVB | | | Unit |
|--|---------------------------------|-------------|------|-------|------------------|
| | | 1080 | 1090 | 10100 | |
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 80 | 90 | 100 | V |
| Average Rectified Forward Current (Rated V_R) $T_C = 133^\circ\text{C}$ | $I_{F(AV)}$ | 10 | | | A |
| Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz) $T_C = 133^\circ\text{C}$ | I_{FRM} | 20 | | | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 150 | | | A |
| Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz) | I_{RRM} | 0.5 | | | A |
| Operating Junction Temperature (Note 1) | T_J | -65 to +175 | | | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -65 to +175 | | | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | | | V/ μs |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------|---------------------------|
| Maximum Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.0 | $^\circ\text{C}/\text{W}$ |
| Maximum Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 60 | $^\circ\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|--------|----------------------------|------|
| Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 10$ Amps, $T_C = 25^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 25^\circ\text{C}$) | V_F | 0.7 0.8 0.85 0.95 | V |
| Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^\circ\text{C}$) (Rated dc Voltage, $T_C = 25^\circ\text{C}$) | i_R | 6.0 0.10 | mA |

- Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MBR1080G, MBR1090G, MBR10100G, NRVB10100G

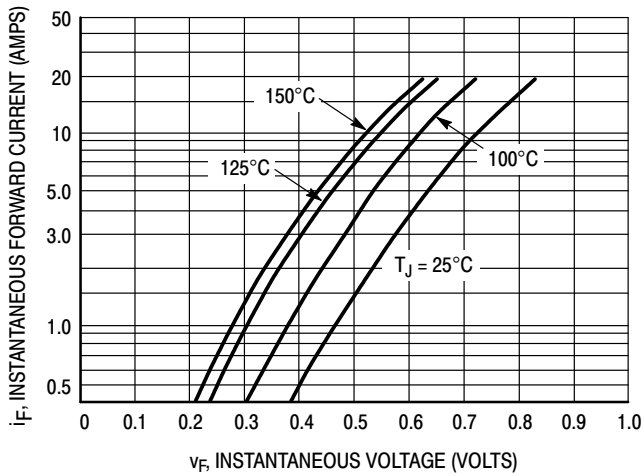


Figure 1. Typical Forward Voltage

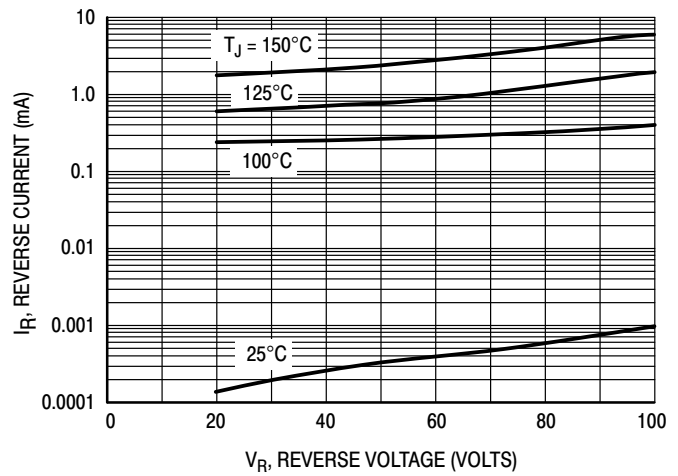


Figure 2. Typical Reverse Current

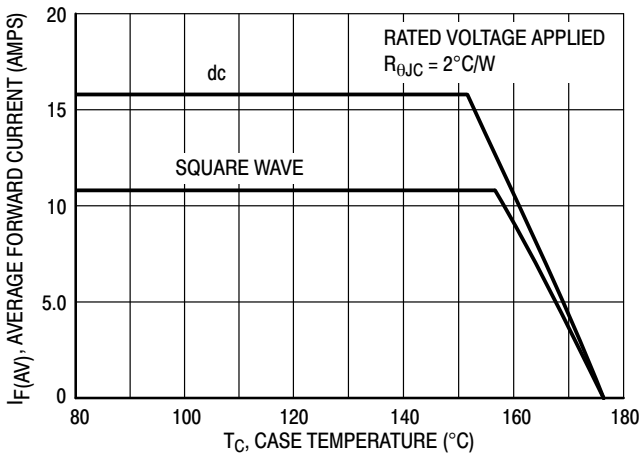


Figure 3. Typical Current Derating, Case

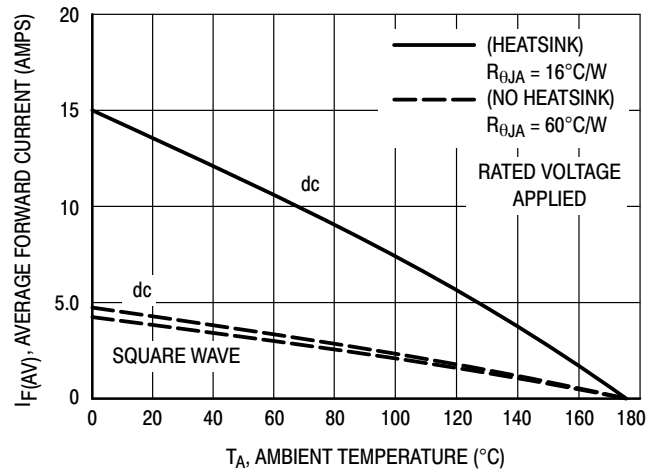


Figure 4. Typical Current Derating, Ambient

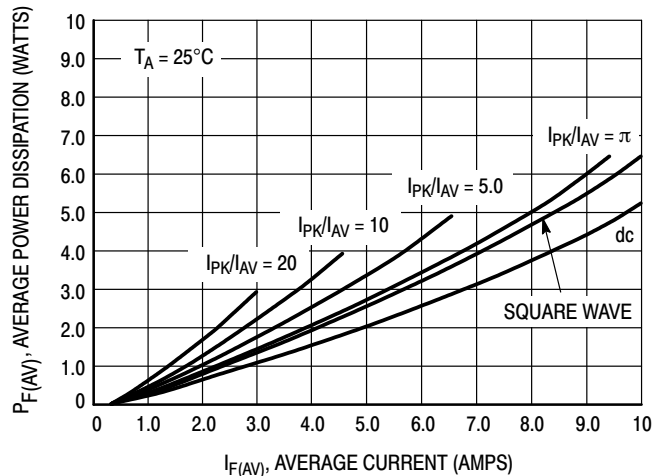
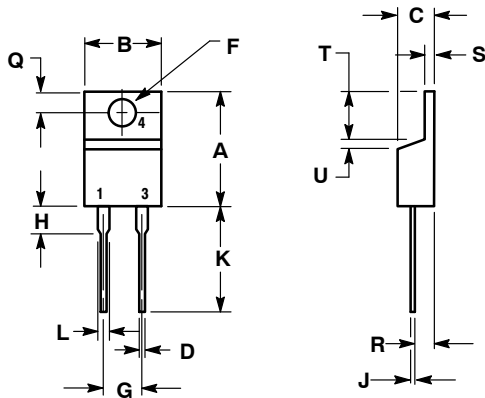


Figure 5. Forward Power Dissipation

MBR1080G, MBR1090G, MBR10100G, NRVB10100G

PACKAGE DIMENSIONS

TO-220
CASE 221B-04
ISSUE E



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.595 | 0.620 | 15.11 | 15.75 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.89 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.190 | 0.210 | 4.83 | 5.33 |
| H | 0.110 | 0.130 | 2.79 | 3.30 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.14 | 1.52 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.14 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.48 |
| U | 0.000 | 0.050 | 0.000 | 1.27 |

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative

www.BDTIC.com/ON/

MBR1080/D